



# PJD70N10

## 100V N-Channel Enhancement Mode MOSFET

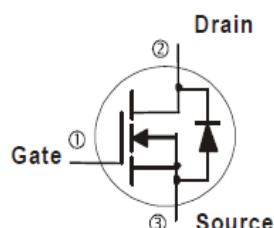
**Voltage      100 V      Current      70 A**

### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V, I_D@20A < 12m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

### Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current  $T_C=25^\circ C$	$I_D$	70	A
		50	
Pulsed Drain Current <sup>(Note 1)</sup>  $T_C=25^\circ C$	$I_{DM}$	175	
Power Dissipation  $T_C=25^\circ C$	$P_D$	125	W
		38	
Continuous Drain Current  $T_A=25^\circ C$	$I_D$	9	A
		7.5	A
Power Dissipation  $T_A=25^\circ C$	$P_D$	2.0	W
Power Dissipation  $T_A=70^\circ C$		1.4	
Single Pulse Avalanche Energy <sup>(Note 6)</sup>	$E_{AS}$	225	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~175	°C
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{\theta JC}$	1.2
	Junction to Ambient	$R_{\theta JA}$	75

- Limited only by Maximum Junction Temperature



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## Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	2.94	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	9.4	12	$m\Omega$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=80V, V_{GS}=0V$	-	-	1.0	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 25V, V_{DS}=0V$	-	$\pm 10$	$\pm 100$	nA
<b>Dynamic</b> <small>(Note 7)</small>						
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=30A,$ $V_{GS}=10V$ <small>(Note 1,2)</small>	-	69	-	nC
Gate-Source Charge	$Q_{gs}$		-	9.8	-	
Gate-Drain Charge	$Q_{gd}$		-	27	-	
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	3061	-	pF
Output Capacitance	$C_{oss}$		-	366	-	
Reverse Transfer Capacitance	$C_{rss}$		-	187	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=30A,$ $V_{GS}=10V, R_G=6.8\Omega$ <small>(Note 1,2)</small>	-	25	-	ns
Turn-On Rise Time	$t_r$		-	66	-	
Turn-Off Delay Time	$t_{d(off)}$		-	76	-	
Turn-Off Fall Time	$t_f$		-	46	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_s$	---	-	-	70	A
Diode Forward Voltage	$V_{SD}$	$I_s=20A, V_{GS}=0V$	-	0.84	1.3	V

### NOTES :

1. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature  $T_J(MAX)=150^\circ C$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25^\circ C$ .
4. The maximum current rating is package limited.
5.  $R_{QJA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. The test condition is  $L=0.5mH, I_{AS}=30A, V_{DD}=25V, V_{GS}=10V$
7. Guaranteed by design, not subject to production testing.



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## TYPICAL CHARACTERISTIC CURVES

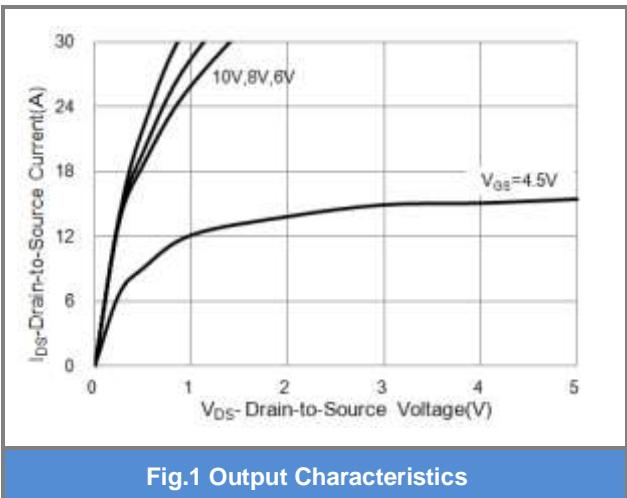


Fig.1 Output Characteristics

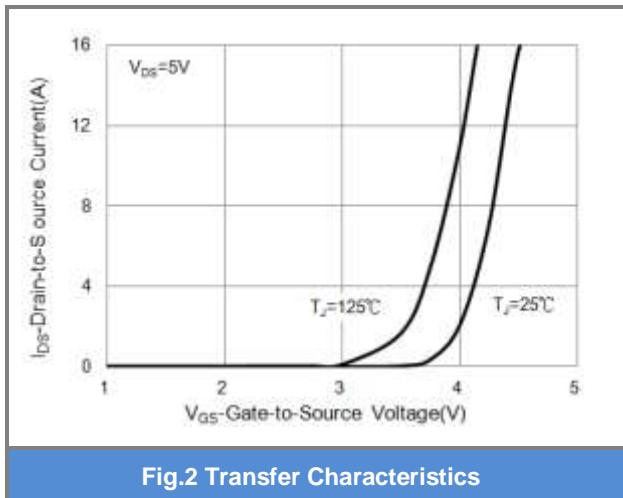


Fig.2 Transfer Characteristics

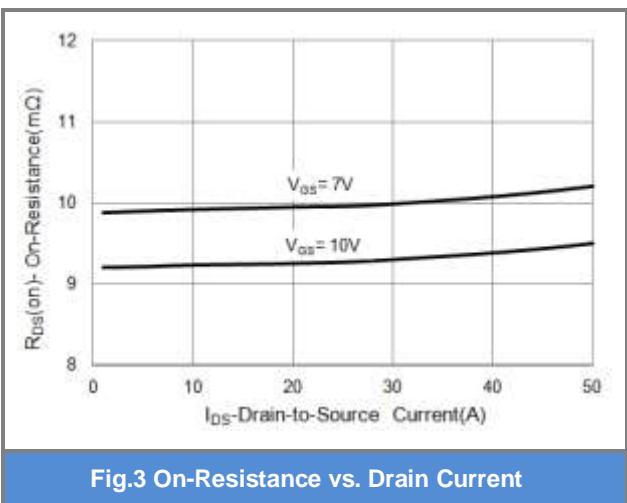


Fig.3 On-Resistance vs. Drain Current

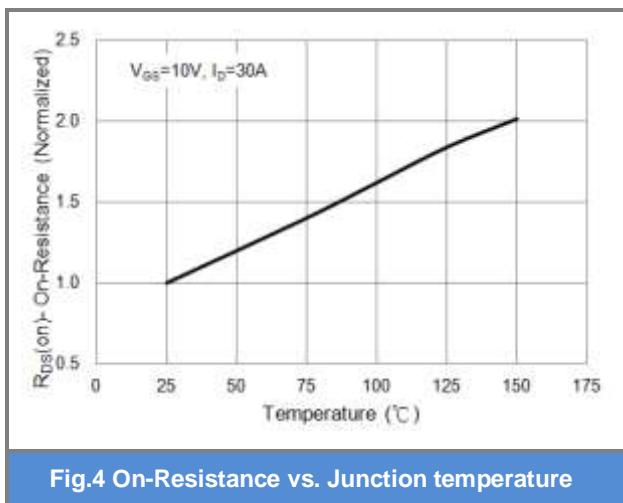


Fig.4 On-Resistance vs. Junction temperature

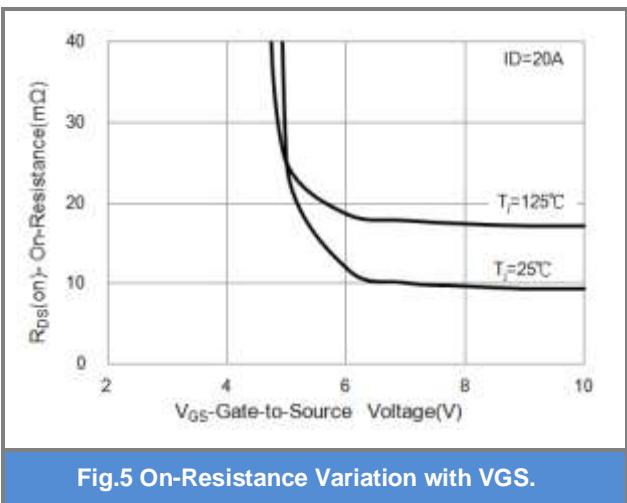


Fig.5 On-Resistance Variation with VGS.

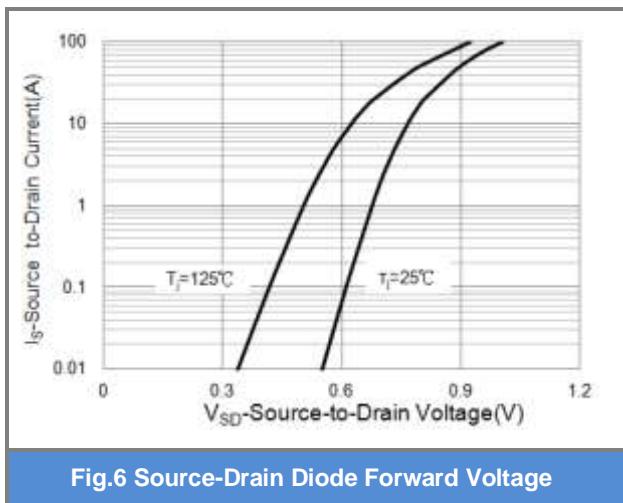
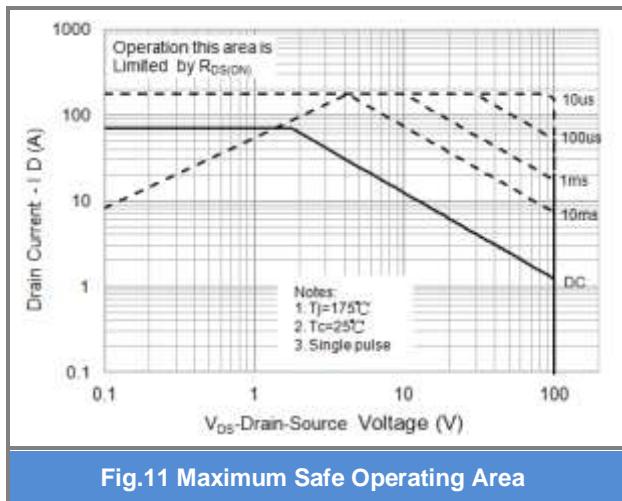
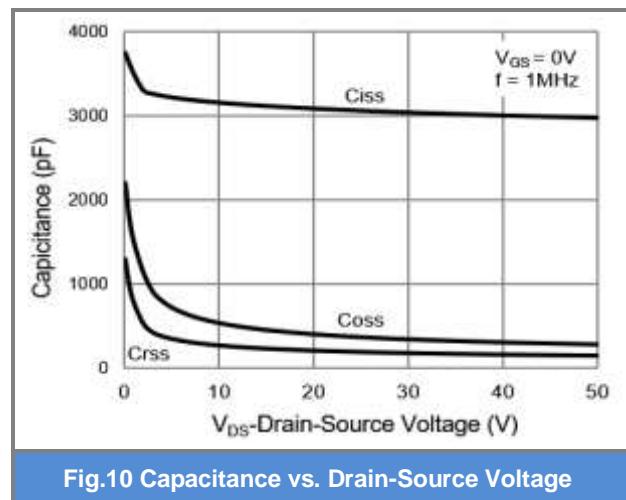
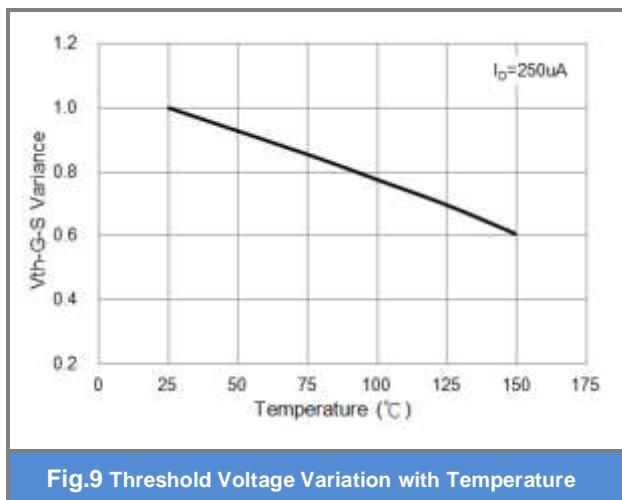
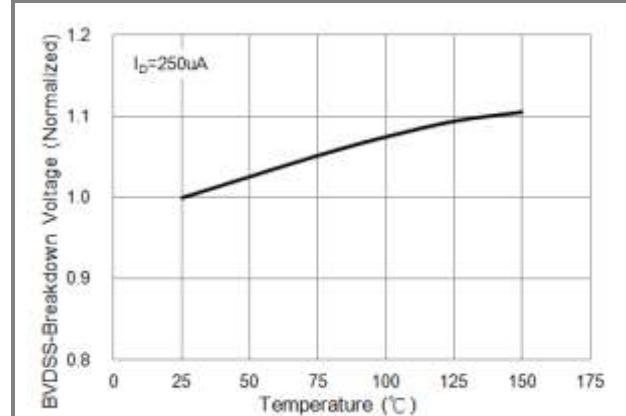
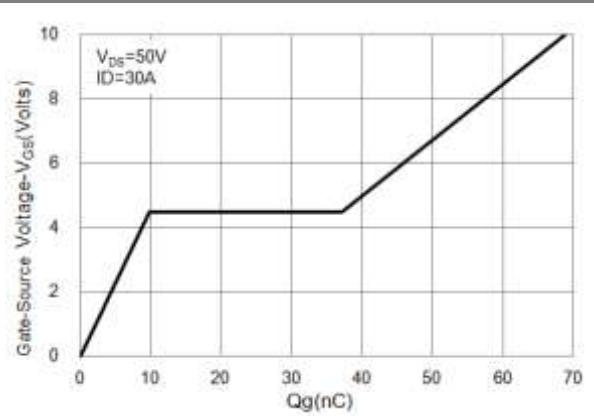


Fig.6 Source-Drain Diode Forward Voltage



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## TYPICAL CHARACTERISTIC CURVES





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## TYPICAL CHARACTERISTIC CURVES

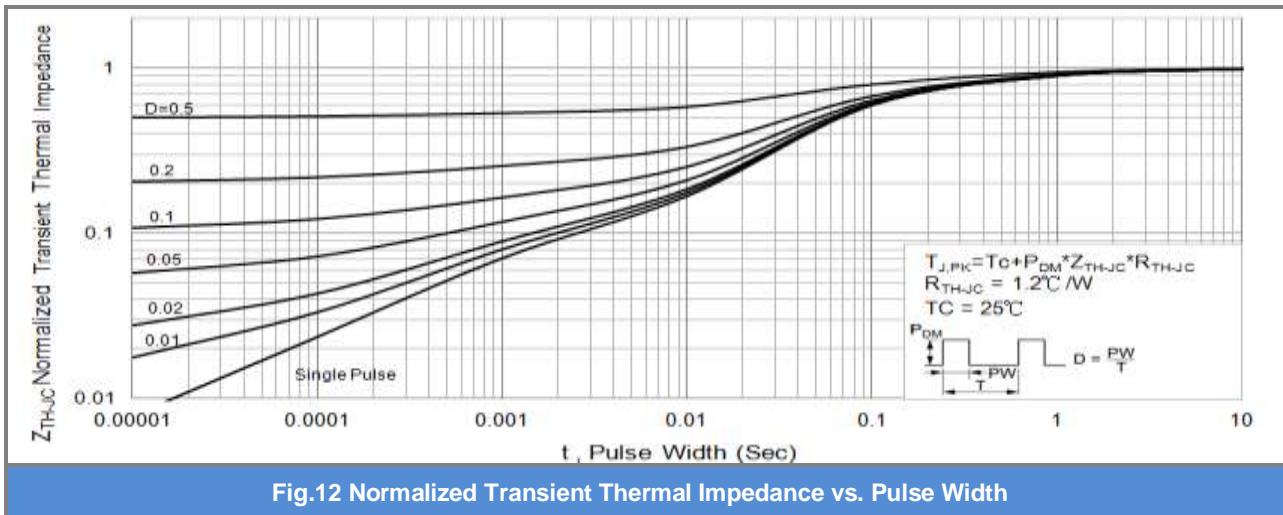
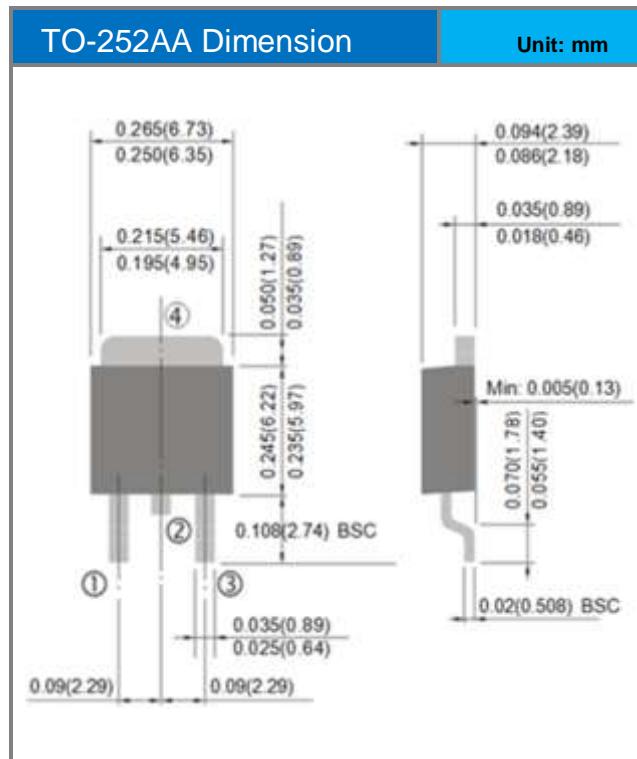


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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## Packaging Information



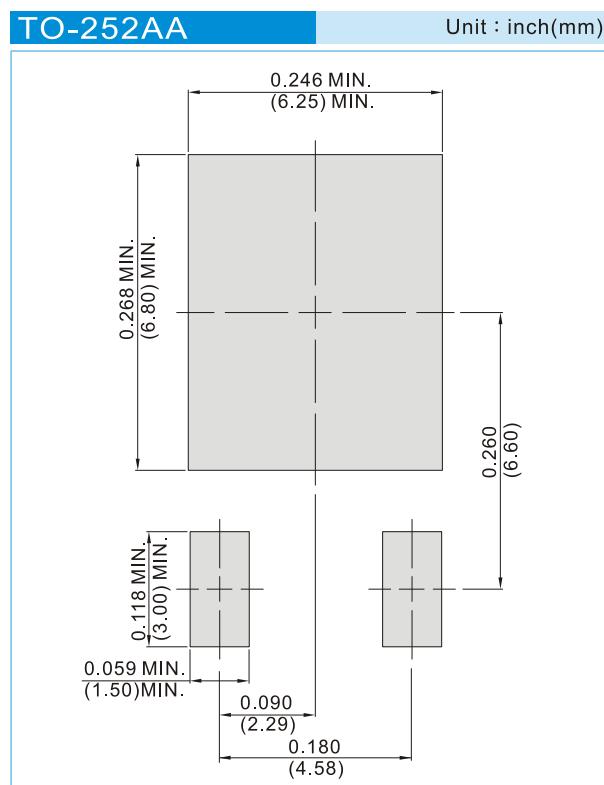


**PJD70N10**

**PART NO** **PACKING CODE** **VERSION**

Part No	Packing Code	Package Type	Packing Type	Marking	Version
PJD70N10	L2_00001	TO-252AA	3,000pcs / 13" reel	D70N10	Halogen free

## MOUNTING PAD LAYOUT





## PJD70N10

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